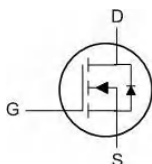
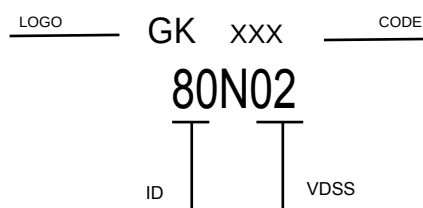


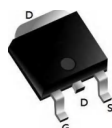
FEATURES

100% EAS Guaranteed
Green Device Available
Super Low Gate Charge
Excellent CdV/dt effect decline
Advanced high cell density Trench
technology

V_{DS} 20 V
 I_D 80 A
 $R_{DS(ON)}$ 3.5 m Ω



Schematic Diagram



TO-252 top view

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	80	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	35	A
I_{DM}	Pulsed Drain Current ²	200	A
EAS	Single Pulse Avalanche Energy ³	58	mJ
I_{AS}	Avalanche Current	41	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	58	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 125	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.6	$^\circ\text{C/W}$

Electrical characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.4	0.7	1.1	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =4.5V, I _D =30A	-	3.5	5	mΩ
		V _{GS} =2.5V, I _D =20A	-	6.5	9	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f = 1.0MHz	-	2500	-	pF
C _{oss}	Output Capacitance		-	407	-	pF
C _{rss}	Reverse Transfer Capacitance		-	386	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =30A, V _{GS} =4.5V	-	32	-	nC
Q _{gs}	Gate-Source Charge		-	3	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	11	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V, I _D =30A, R _{GEN} =3Ω, V _{GS} =4.5V	-	17	-	ns
t _r	Turn-on Rise Time		-	49	-	ns
t _{d(off)}	Turn-off Delay Time		-	74	-	ns
t _f	Turn-off Fall Time		-	26	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	80	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =30A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=10V$, $V_G=4.5V$, $L=0.5mH$, $R_G=25\Omega$, $I_{AS}=15A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

RATING AND CHARACTERISTIC CURVES

Figure1: Output Characteristics

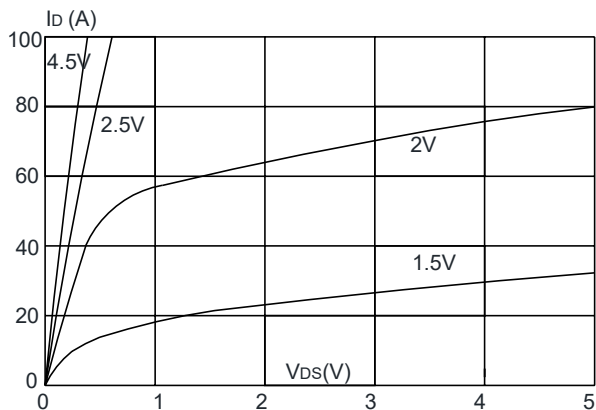


Figure 2: Typical Transfer Characteristics

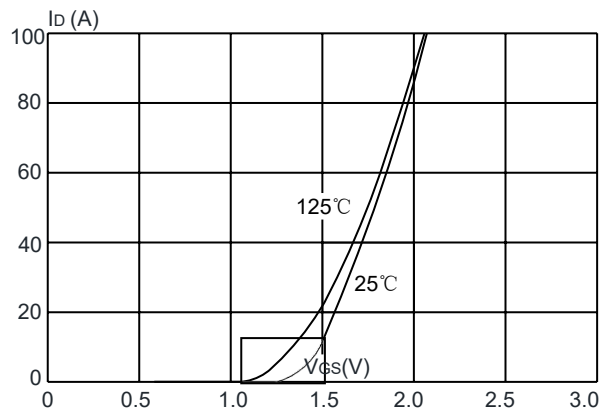


Figure 3: On-resistance vs. Drain Current

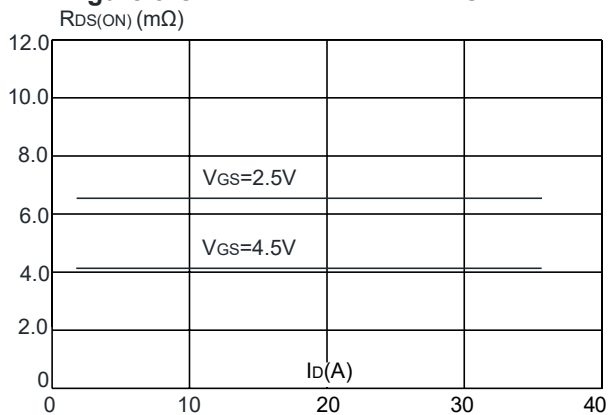


Figure 4: Body Diode Characteristics

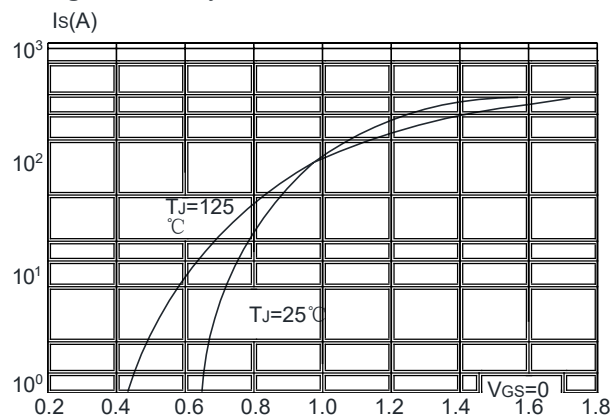


Figure 5: Gate Charge Characteristics

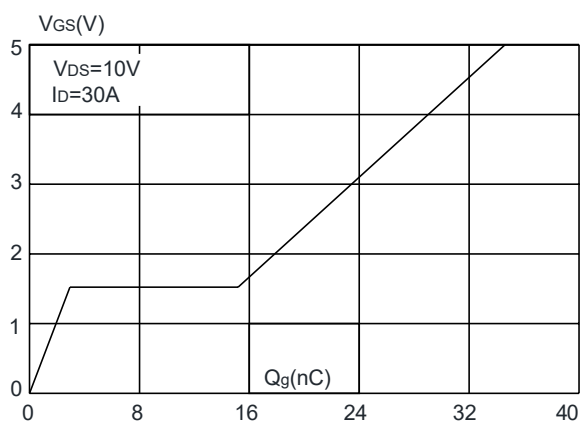
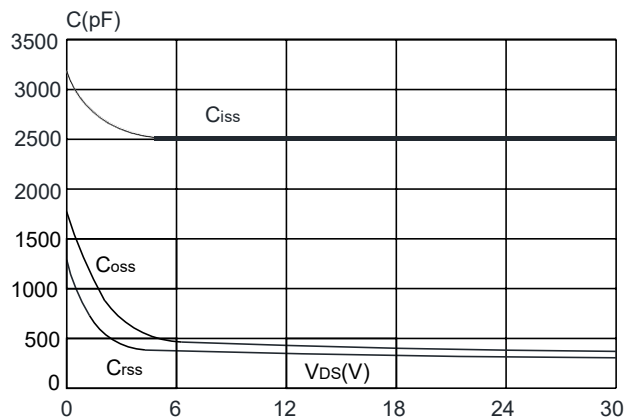


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

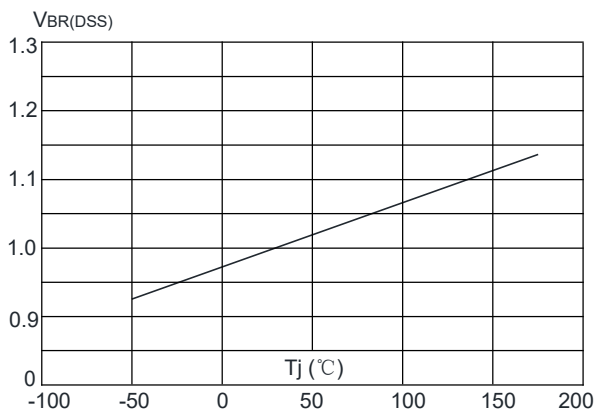


Figure 8: Normalized on Resistance vs. Junction Temperature

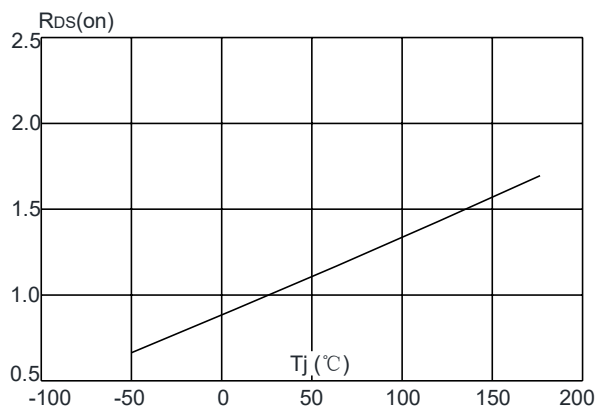


Figure 9: Maximum Safe Operating Area

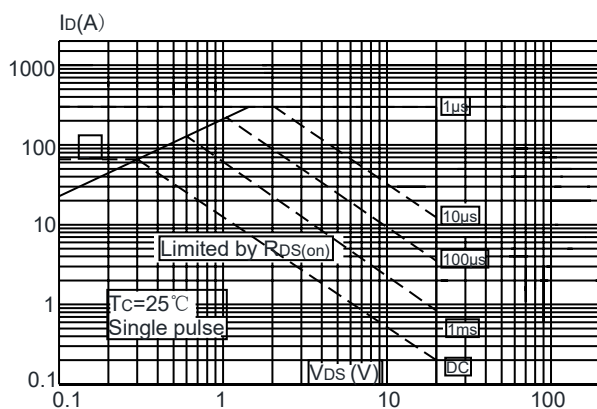


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

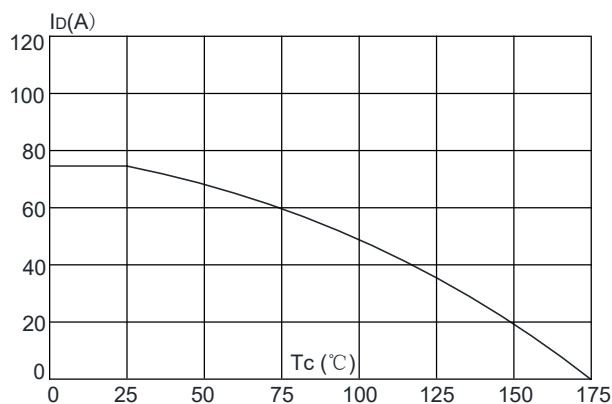
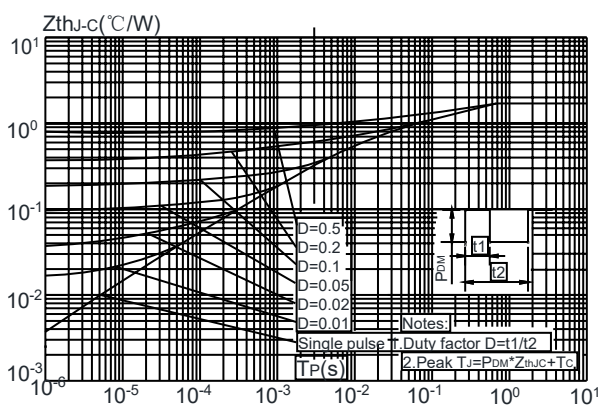
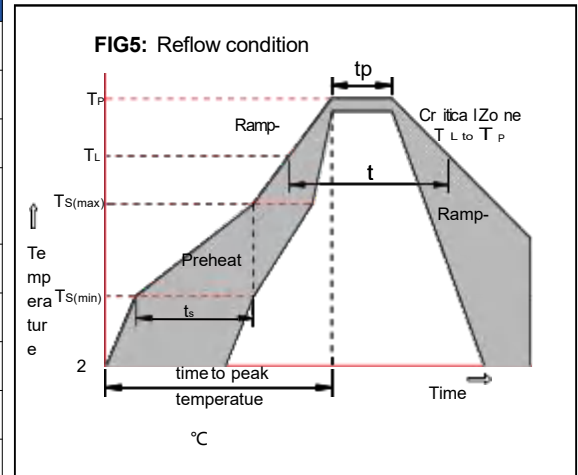


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



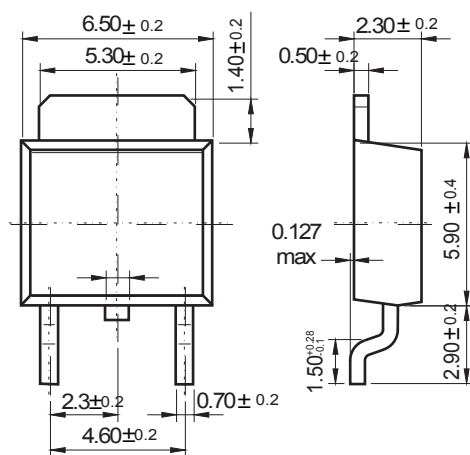
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max ($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

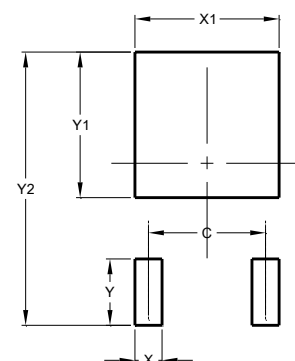


Package Dimensions & Suggested Pad Layout

TO-252

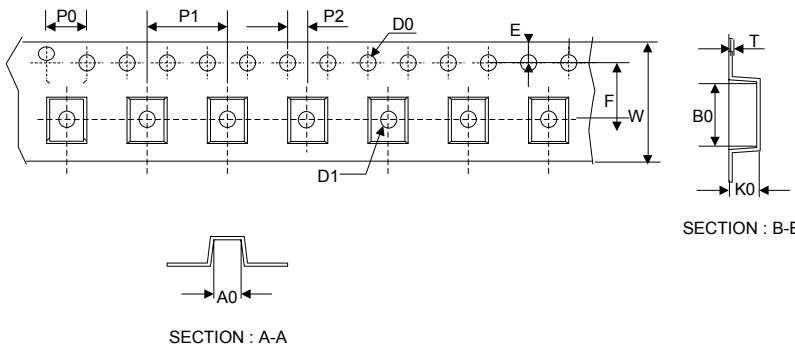
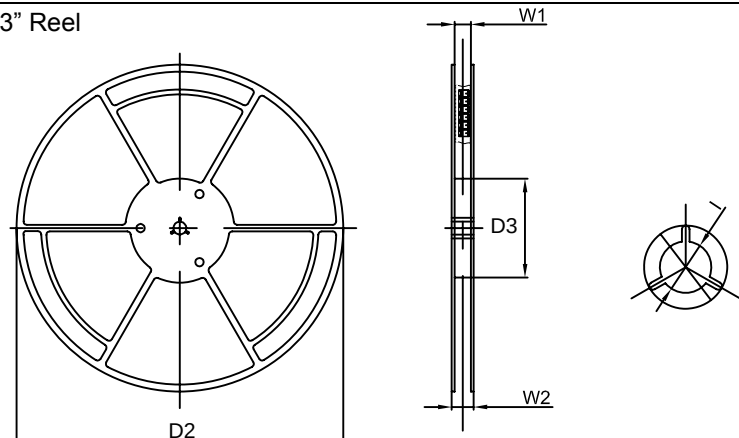


Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

Tape & reel specification

Tape		Symbol	Dimension (mm)
 SECTION : A-A SECTION : B-B		P0	4.00±0.20
		P1	8.00±0.20
		P2	2.00±0.20
		D0	1.55±0.15
		D1	1.55±0.20
		E	1.75±0.20
		F	7.50±0.20
		W	16.00±0.20
		A0	7.10±0.20
		B0	10.50±0.20
		K0	2.70±0.20
		T	0.30±0.10
		D2	330.0±5.0
		D3	100.0±4.0
		W1	20.0±5.0
		W2	25.0±5.0
13" Reel		I	13.0±2.0
		Quantity: 2500PCS	